



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Mohamed N. Darwish et al.
Assignee: Siliconix Incorporated
Title: TRENCH MIS DEVICE WITH REDUCED GATE-TO-DRAIN CAPACITANCE
Serial No.: 09/927,320 Filing Date: August 10, 2001
Examiner: Edgardo Ortiz Group Art Unit: 2815
Docket No.: M-11671 US

San Jose, California
August 28, 2002

COMMISSIONER FOR PATENTS
Washington, D. C. 20231

RESPONSE TO OFFICE ACTION

Dear Sir:

Applicants submit this amendment in response to the Office Action in this case having a mailing date of June 3, 2002.

IN THE CLAIMS

Please amend Claims 1-4 and 7-18 as follows:

1. (amended) A metal-insulator-semiconductor device, comprising:
- a semiconductor substrate defining a trench extending into said substrate from a surface of said substrate;
 - a source region of a first conductivity type adjacent to a sidewall of said trench and to said surface;
 - a body region of a second conductivity type opposite to said first conductivity type adjacent to said source region and to said sidewall; and
 - a drain region of said first conductivity type adjacent to said body region and to said sidewall,

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